

# 5 V TTL to Differential PECL Translator

## MC10ELT20

### Description

The MC10ELT20 is a TTL to differential PECL translator. Because PECL (Positive ECL) levels are used, only +5 V and ground are required. The small outline 8-lead package and the single gate of the ELT20 makes it ideal for those applications where space, performance, and low power are at a premium.

The 100 Series contains temperature compensation.

### Features

- 1.2 ns Typical Propagation Delay
- PNP TTL Inputs for Minimal Loading
- Flow Through Pinouts
- Operating Range:  $V_{CC} = 4.75$  V to 5.25 V with  $GND = 0$  V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



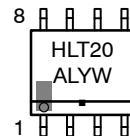
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SO-8  
D SUFFIX  
CASE 751

### MARKING DIAGRAMS\*



H = MC10  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
■ = Pb-Free Package

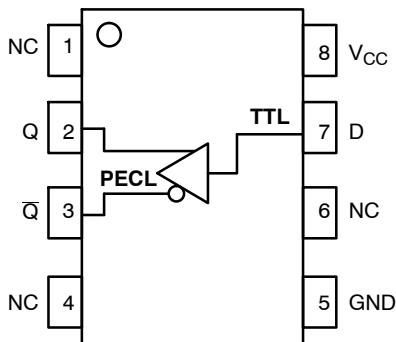
(Note: Microdot may be in either location)

\*For additional marking information, refer to Application Note [AND8002/D](#).

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC10ELT20DG	SO-8 (Pb-Free)	98 Units / Tube
MC10ELT20DR2G	SO-8 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



**Figure 1. 8-Lead Pinout (Top View) and Logic Diagram**

**Table 1. PIN DESCRIPTION**

Pin	Function
Q, Q̄	PECL Differential Outputs*
D	TTL Input
V <sub>CC</sub>	Positive Supply
GND	Ground
NC	No Connect

\*Output state undetermined when inputs are open.

**Table 2. ATTRIBUTES**

Characteristics	Value
Internal Input Pulldown Resistor	N/A
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model	> 4 kV > 200 V
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SO-8	Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	51 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note AND8003/D.

**Table 3. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V <sub>CC</sub>	Positive Power Supply	GND = 0 V		7	V
V <sub>IN</sub>	Input Voltage	GND = 0 V	V <sub>I</sub> 3 ≤ V <sub>CC</sub>	7	V
I <sub>out</sub>	Output Current	Continuous Surge		50 100	mA mA
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
θ <sub>JA</sub>	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SO-8 SO-8	190 130	°C/W °C/W
θ <sub>JC</sub>	Thermal Resistance (Junction-to-Case)	Standard Board	SO-8	41 to 44	°C/W
T <sub>sol</sub>	Wave Solder	Pb-Free	< 3 s @ 260°C	265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**Table 4. 10ELT SERIES PECL DC CHARACTERISTICS**  $V_{CC} = 5.0$  V; GND = 0.0 V (Note 2)

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
$I_{CC}$	Power Supply Current			16			16			16	mA
$V_{OH}$	Output HIGH Voltage (Note 3)	3920	4010	4110	4020	4105	4190	4090	4185	4280	mV
$V_{OL}$	Output LOW Voltage (Note 3)	3050	3200	3350	3050	3210	3370	3050	3227	3405	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

2. Output parameters vary 1:1 with  $V_{CC}$ .  $V_{CC}$  can vary  $\pm 0.25$  V.

3. Outputs are terminated through a  $50 \Omega$  resistor to  $V_{CC} - 2$  V.

**Table 5. TTL INPUT DC CHARACTERISTICS**  $V_{CC} = 4.7$  V to 5.27 V;  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$ 

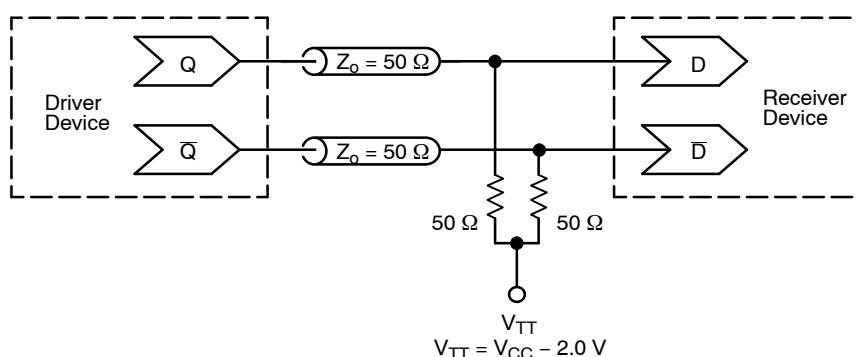
Symbol	Characteristic	Condition			Min		Typ		Max		Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
$I_{IH}$	Input HIGH Current	$V_{IN} = 2.7$ V								20	$\mu\text{A}$
$I_{IHH}$	Input HIGH Current	$V_{IN} = 7.0$ V								100	$\mu\text{A}$
$I_{IL}$	Input LOW Current	$V_{IN} = 0.5$ V								-0.6	mA
$V_{IK}$	Input Clamp Diode Voltage	$I_{IN} = -18$ mA								-1.2	V
$V_{IH}$	Input HIGH Voltage				2.0						V
$V_{IL}$	Input LOW Voltage									0.8	V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

**Table 6. AC CHARACTERISTICS**  $V_{CC} = 4.75$  V to 5.25 V; GND = 0.0 V

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
$f_{max}$	Maximum Toggle Frequency	100			100			100			MHz
$t_{PLH}$	Propagation Delay 1.5 V to 50%	0.6	0.82	1.2	0.6	0.82	1.25	0.6	0.83	1.35	ns
$t_{PHL}$	Propagation Delay 1.5 V to 50%	0.4		1.0	0.5	0.8	1.1	0.7		1.30	ns
$t_{JITTER}$	Cycle-to-Cycle Jitter		TBD			TBD			TBD		ps
$t_r/t_f$	Output Rise/Fall Time (20–80%)	0.15		1.5	0.15		1.5	0.15		1.5	ns

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

**Figure 2. Typical Termination for Output Driver and Device Evaluation**  
(See Application Note AND8020/D – Termination of ECL Logic Devices.)

## Resource Reference of Application Notes

- AN1405/D** – ECL Clock Distribution Techniques
- AN1406/D** – Designing with PECL (ECL at +5.0 V)
- AN1503/D** – ECLinPS™ I/O SPiCE Modeling Kit
- AN1504/D** – Metastability and the ECLinPS Family
- AN1568/D** – Interfacing Between LVDS and ECL
- AN1672/D** – The ECL Translator Guide
- AND8001/D** – Odd Number Counters Design
- AND8002/D** – Marking and Date Codes
- AND8020/D** – Termination of ECL Logic Devices
- AND8066/D** – Interfacing with ECLinPS
- AND8090/D** – AC Characteristics of ECL Devices

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

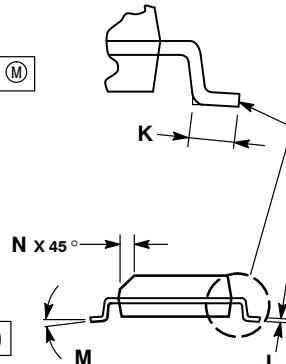
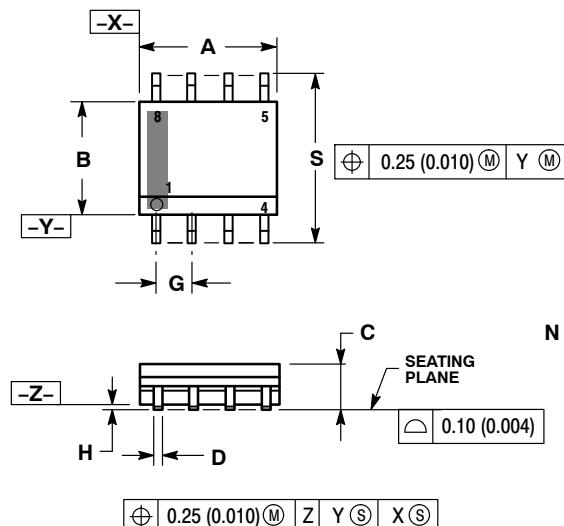
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SCALE 1:1

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N x 45°

M

J

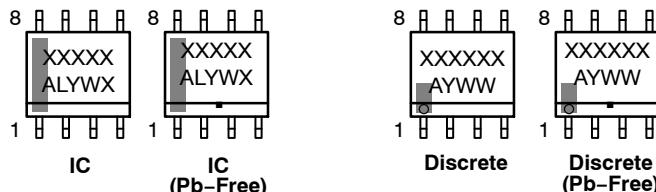
⊕ 0.25 (0.010) M Z Y S X S

### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

### GENERIC MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
▪ = Pb-Free Package

XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SCALE 6:1 (mm  
inches)

STYLES ON PAGE 2

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DATE 16 FEB 2011

STYLE 1: PIN 1. Emitter 2. Collector 3. Collector 4. Emitter 5. Emitter 6. Base 7. Base 8. Emitter	STYLE 2: PIN 1. Collector, Die #1 2. Collector, #1 3. Collector, #2 4. Collector, #2 5. Base, #2 6. Emitter, #2 7. Base, #1 8. Emitter, #1	STYLE 3: PIN 1. Drain, Die #1 2. Drain, #1 3. Drain, #2 4. Drain, #2 5. Gate, #2 6. Source, #2 7. Gate, #1 8. Source, #1	STYLE 4: PIN 1. Anode 2. Anode 3. Anode 4. Anode 5. Anode 6. Anode 7. Anode 8. Common Cathode
STYLE 5: PIN 1. Drain 2. Drain 3. Drain 4. Drain 5. Gate 6. Gate 7. Source 8. Source	STYLE 6: PIN 1. Source 2. Drain 3. Drain 4. Source 5. Source 6. Gate 7. Gate 8. Source	STYLE 7: PIN 1. Input 2. External Bypass 3. Third Stage Source 4. Ground 5. Drain 6. Gate 3 7. Second Stage Vd 8. First Stage Vd	STYLE 8: PIN 1. Collector, Die #1 2. Base, #1 3. Base, #2 4. Collector, #2 5. Collector, #2 6. Emitter, #2 7. Emitter, #1 8. Collector, #1
STYLE 9: PIN 1. Emitter, Common 2. Collector, Die #1 3. Collector, Die #2 4. Emitter, Common 5. Emitter, Common 6. Base, Die #2 7. Base, Die #1 8. Emitter, Common	STYLE 10: PIN 1. Ground 2. Bias 1 3. Output 4. Ground 5. Ground 6. Bias 2 7. Input 8. Ground	STYLE 11: PIN 1. Source 1 2. Gate 1 3. Source 2 4. Gate 2 5. Drain 2 6. Drain 2 7. Drain 1 8. Drain 1	STYLE 12: PIN 1. Source 2. Source 3. Source 4. Gate 5. Drain 6. Drain 7. Drain 8. Drain
STYLE 13: PIN 1. N.C. 2. Source 3. Source 4. Gate 5. Drain 6. Drain 7. Drain 8. Drain	STYLE 14: PIN 1. N-Source 2. N-Gate 3. P-Source 4. P-Gate 5. P-Drain 6. P-Drain 7. N-Drain 8. N-Drain	STYLE 15: PIN 1. Anode 1 2. Anode 1 3. Anode 1 4. Anode 1 5. Cathode, Common 6. Cathode, Common 7. Cathode, Common 8. Cathode, Common	STYLE 16: PIN 1. Emitter, Die #1 2. Base, Die #1 3. Emitter, Die #2 4. Base, Die #2 5. Collector, Die #2 6. Collector, Die #2 7. Collector, Die #1 8. Collector, Die #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. Anode 2. Anode 3. Source 4. Gate 5. Drain 6. Drain 7. Cathode 8. Cathode	STYLE 19: PIN 1. Source 1 2. Gate 1 3. Source 2 4. Gate 2 5. Drain 2 6. Mirror 2 7. Drain 1 8. Mirror 1	STYLE 20: PIN 1. Source (N) 2. Gate (N) 3. Source (P) 4. Gate (P) 5. Drain 6. Drain 7. Drain 8. Drain
STYLE 21: PIN 1. Cathode 1 2. Cathode 2 3. Cathode 3 4. Cathode 4 5. Cathode 5 6. Common Anode 7. Common Anode 8. Cathode 6	STYLE 22: PIN 1. I/O Line 1 2. Common Cathode/VCC 3. Common Cathode/VCC 4. I/O Line 3 5. Common Anode/GND 6. I/O Line 4 7. I/O Line 5 8. Common Anode/GND	STYLE 23: PIN 1. Line 1 IN 2. Common Anode/GND 3. Common Anode/GND 4. Line 2 IN 5. Line 2 OUT 6. Common Anode/GND 7. Common Anode/GND 8. Line 1 OUT	STYLE 24: PIN 1. Base 2. Emitter 3. Collector/Anode 4. Collector/Anode 5. Cathode 6. Cathode 7. Collector/Anode 8. Collector/Anode
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. Enable 4. ILIMIT 5. Source 6. Source 7. Source 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBUCK 7. VBUCK 8. VIN
STYLE 29: PIN 1. Base, Die #1 2. Emitter, #1 3. Base, #2 4. Emitter, #2 5. Collector, #2 6. Collector, #2 7. Collector, #1 8. Collector, #1	STYLE 30: PIN 1. Drain 1 2. Drain 1 3. Gate 2 4. Source 2 5. Source 1/Drain 2 6. Source 1/Drain 2 7. Source 1/Drain 2 8. Gate 1		

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